

N-channel 30 V 9.8 m Ω logic level MOSFET in LFPAK33 using NextPower Technology

Rev. 3 — 15 June 2012

Product data sheet

1. Product profile

1.1 General description

Logic level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Low parasitic inductance and resistance
- Optimised for 4.5V Gate drive utilising NextPower Superjunction technology
- Ultra low QG, QGD, & QOSS for high system efficiencies at low and high loads

1.3 Applications

- DC-to-DC converters
- Load switching

Synchronous buck regulator

1.4 Quick reference data

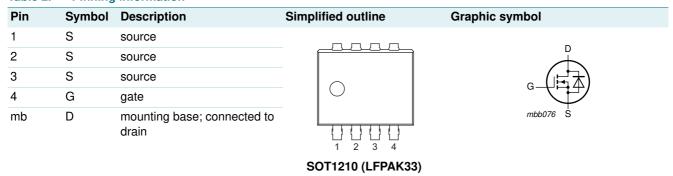
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25 ^{\circ}C$	-	-	30	V
I _D	drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V; see \underline{Figure 1}$	-	-	50	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	45	W
T _j	junction temperature		-55	-	175	°C
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 10	-	10.65	12.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 10	-	8.5	9.8	mΩ
Dynamic char	acteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 4.5 \text{ V}$; $I_D = 15 \text{ A}$; $V_{DS} = 15 \text{ V}$; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	1.5	-	nC
$Q_{G(tot)}$	total gate charge	$V_{GS} = 4.5 \text{ V}$; $I_D = 15 \text{ A}$; $V_{DS} = 15 \text{ V}$; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	5	-	nC



2. Pinning information

Table 2. Pinning information



3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN9R8-30MLC	LFPAK33	Plastic single ended surface mounted package (LFPAK33); 4 leads	SOT1210

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25 ^{\circ}C$	-	30	V
V_{GS}	gate-source voltage		-20	20	V
I_D	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{Model}}$	-	50	Α
		$V_{GS} = 10 \text{ V}; T_{mb} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{\text{ Figure 1}}$	-	36	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; see Figure 4	-	202	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	45	W
T_{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
V_{ESD}	electrostatic discharge voltage	MM (JEDEC JESD22-A115)	140	-	٧
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	41	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	202	Α
Avalanche ru	ıggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 50 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω; unclamped; see <u>Figure 3</u>	-	8	mJ

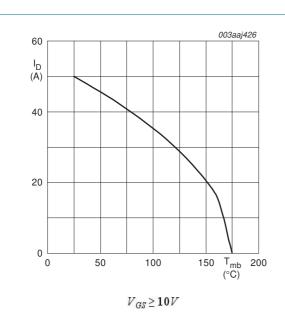


Fig 1. Continuous drain current as a function of mounting base temperature

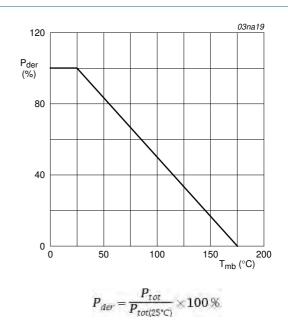
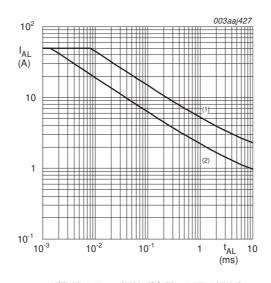
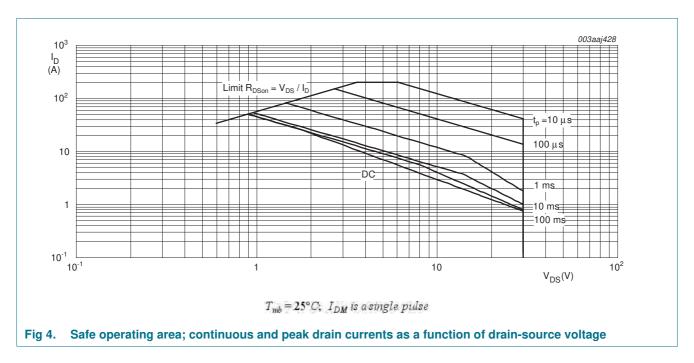


Fig 2. Normalized total power dissipation as a function of mounting base temperature



(1) $T_{j (init)} = 25^{\circ}C$; (2) $T_{j (init)} = 100^{\circ}C$

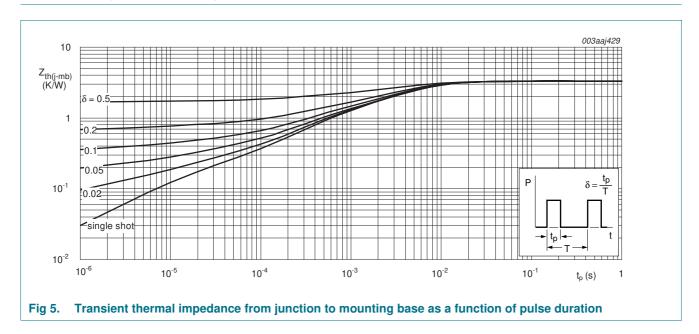
Fig 3. Single pulse avalanche rating; avalanche current as a function of avalanche time



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	3.1	3.32	K/W



6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara				7.5	2	
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _i = 25 °C	30	-	_	V
(BH)B00	breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{V}; T_i = -55 ^{\circ}\text{C}$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.3	1.64	1.95	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature		-	-4	-	mV/k
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μΑ
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 10	-	10.65	12.4	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ °C};$ see Figure 11; see Figure 10	-	-	21.1	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 10	-	8.5	9.8	mΩ
		$V_{GS} = 10 \text{ V}$; $I_D = 15 \text{ A}$; $T_j = 150 \text{ °C}$; see Figure 11; see Figure 10	-	-	16.75	mΩ
R _G	gate resistance	f = 1 MHz	0.9	1.8	3.6	Ω
Dynamic cl	haracteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 15 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 12; see Figure 13	-	10.9	-	nC
		I_D = 15 A; V_{DS} = 15 V; V_{GS} = 4.5 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	5	-	nC
		$I_D = 0 A; V_{DS} = 0 V; V_{GS} = 10 V$	-	10	-	nC
Q _{GS}	gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 12</u> ; see <u>Figure 13</u>	-	1.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	8.0	-	nC
Q_{GD}	gate-drain charge		-	1.5	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 15 A; V _{DS} = 15 V; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	3.1	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;	-	690	-	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	170	-	pF
C _{rss}	reverse transfer capacitance		-	52	-	pF

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$t_{d(on)}$	turn-on delay time	$\begin{split} V_{DS} &= 15 \text{ V}; \text{ R}_{L} = 1 \Omega; V_{GS} = 4.5 \text{ V}; \\ R_{G(ext)} &= 5 \Omega \end{split}$	-	7.4	-	ns
t _r	rise time		-	7.7	-	ns
t _{d(off)}	turn-off delay time		-	11.7	-	ns
t _f	fall time		-	5.3	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$	-	4.9	-	nC
Source-drai	in diode					
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see Figure 15	-	0.84	1.1	V
t _{rr}	reverse recovery time	$I_S = 15 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	12.9	-	ns
Q _r	recovered charge	V _{DS} = 15 V	-	5.3	-	nC
ta	reverse recovery rise time	$V_{GS} = 0 \text{ V; } I_S = 15 \text{ A; } dI_S/dt = -100 \text{ A/}\mu\text{s;}$ $V_{DS} = 15 \text{ V; see } \frac{\text{Figure 16}}{\text{Missing 1}}$	-	7.9	-	ns
t _b	reverse recovery fall time		-	5	-	ns

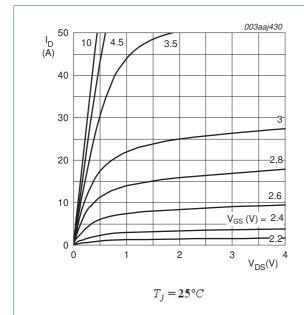


Fig 6. Output characteristics; drain current as a function of drain-source voltage; typical values

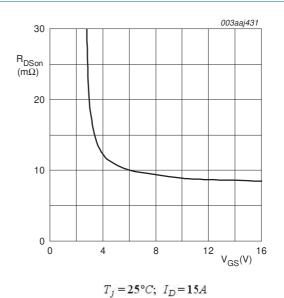


Fig 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

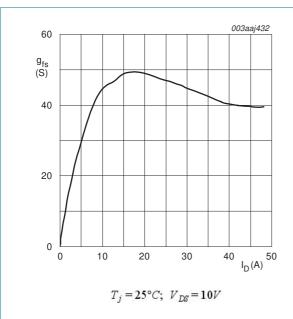


Fig 8. Forward transconductance as a function of drain current; typical values

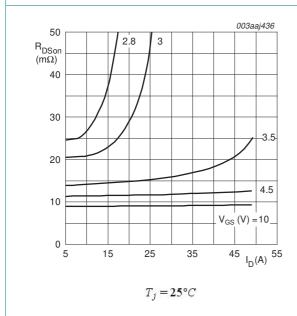


Fig 10. Drain-source on-state resistance as a function of drain current; typical values

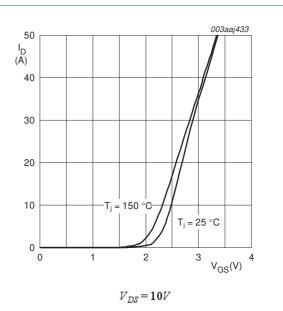


Fig 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

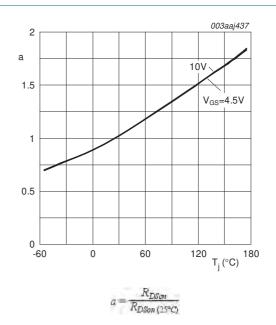


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

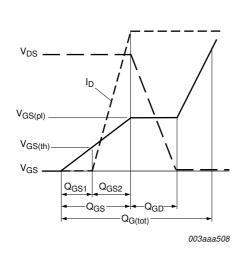


Fig 12. Gate charge waveform definitions

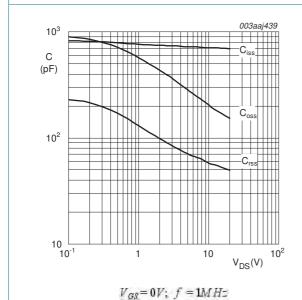
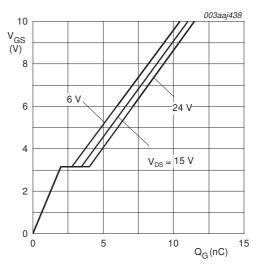


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



 $T_j = 25^{\circ}C; I_D = 15A$

Fig 13. Gate-source voltage as a function of gate charge; typical values

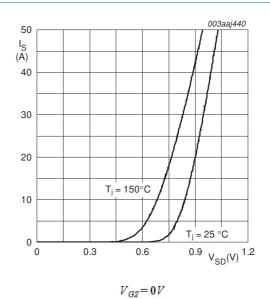
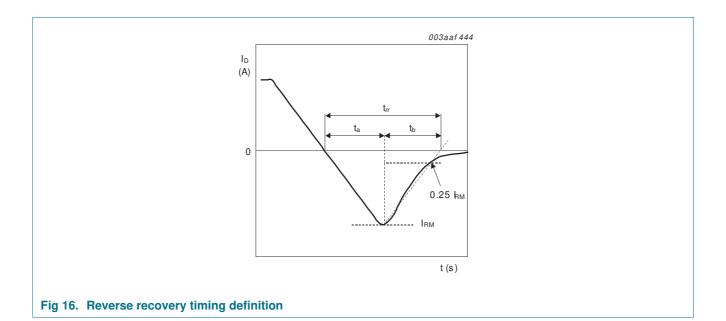


Fig 15. Source current as a function of source-drain voltage; typical values



7. Package outline

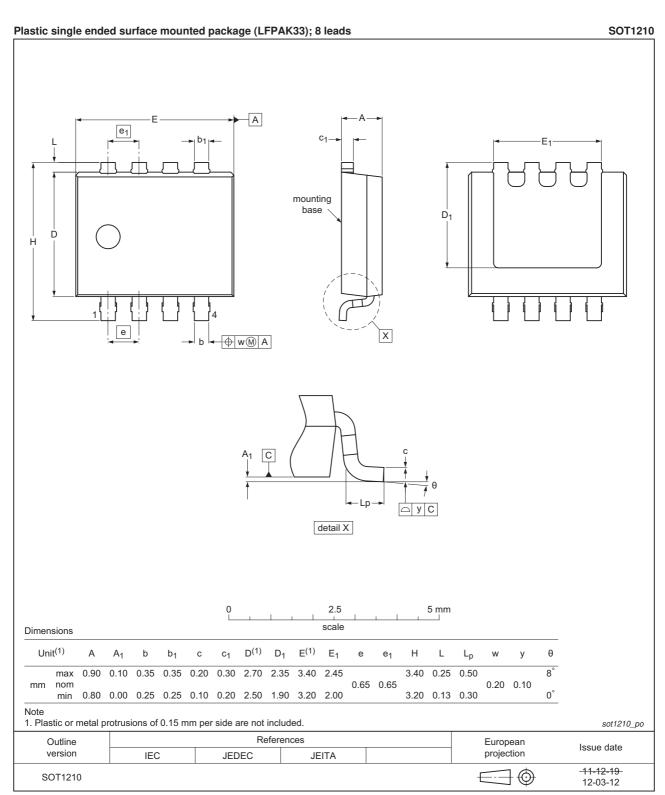


Fig 17. Package outline SOT1210 (LFPAK33)

PSMN9R8-30MLC

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N-channel 30 V 9.8 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN9R8-30MLC v.3	20120615	Product data sheet	-	PSMN9R8-30MLC v.2
Modifications:	Status changed froVarious changes to	m objective to product. content.		
PSMN9R8-30MLC v.2	20120607	Objective data sheet	-	PSMN9R8-30MLC v.1

N-channel 30 V 9.8 mΩ logic level MOSFET in LFPAK33 using NextPower Technology

9. Legal information

9.1 Data sheet status

Document status[1] [2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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